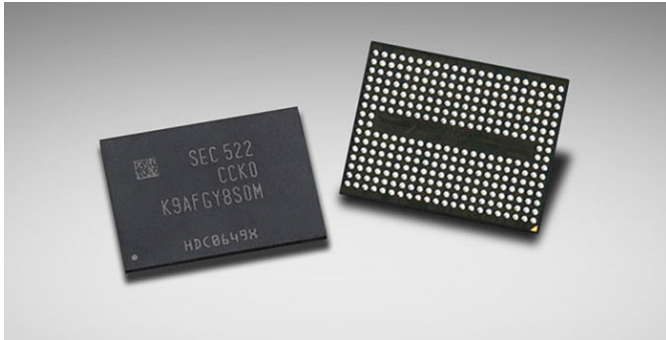


Samsung Produces 256-Gb 3D V-NAND

Written by Marco Attard
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Samsung starts mass production of 3rd generation 256-gigabit (Gb) 3D Vertical NAND (V-NAND) flash memory based on 48 layers of 3-bit multi-level-cell (MLC) arrays for SSD use.



The announcement takes place just a week after the revelation of [256Gb 48-layer BiCS 3D NAND flash from Toshiba and Samsung](#).

In any case, according to Samsung 256Gb 3rd generation 3D V-NAND doubles the density of conventional 128Gb NAND flash chips by enabling up to 32GB of memory storage on a single die, making it ideal for use in multi-terabyte SSDs.

The chips also use up to 30% less power than previous generation when storing the same amount of power, while promising 40% more productivity.

Samsung says it will soon launch consumer SSDs with capacities reaching 2TB and above, as well as high-density SSDs with PCIe NVMe and SAS interfaces for the enterprise and datacentre storage sectors.

Go [Samsung Begins Mass Producing 256Gb 3D V-NAND Flash Memory](#)